

WEST

Freeform Search

Database:

US Patents Full-Text Database
 US Pre-Grant Publication Full-Text Database
 JPO Abstracts Database
 EPO Abstracts Database
 Derwent World Patents Index
 IBM Technical Disclosure Bulletins

Term:

Display: Documents in **Display Format:** Starting with Number

Generate: Hit List Hit Count Side by Side Image

[Main Menu](#) | [Show S Numbers](#) | [Edit S Numbers](#) | [Preferences](#) | [Cases](#)

Search History

DATE: Wednesday, September 25, 2002 [Printable Copy](#) [Create Case](#)Set Name Query
side by sideHit Count Set Name
result set

<i>DB=USPT; PLUR=YES; OP=OR</i>		
<u>L10</u> L9 and substrate and silicon	1250	<u>L10</u>
<u>L9</u> "(110)".clm.	10952	<u>L9</u>
<u>L8</u> L7 and ((hydrogenated near4 nitride) or (oxynitride))	94	<u>L8</u>
<u>L7</u> glass with ((passivation or base or underlayer or blocking) near4 (layer or film)) and (TFT\$1 or (thin adj film))	2025	<u>L7</u>
<u>L6</u> fonash.in.	18	<u>L6</u>
<u>L5</u> L4 not (semiconductor and energy and laboratory)	105	<u>L5</u>
<u>L4</u> L3 and semiconductor	365	<u>L4</u>
<u>L3</u> L2 and oxide	1174	<u>L3</u>
<u>L2</u> L1 and (nickel with solution)	1318	<u>L2</u>
<u>L1</u> amorphous same crystal\$8	40932	<u>L1</u>

END OF SEARCH HISTORY